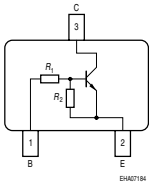


**NPN Silicon Digital Transistor**

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ( $R_1 = 100k\Omega$  ,  $R_2 = 100k\Omega$  )


**BCR101F/L3  
BCR101T**


Type	Marking	Pin Configuration						Package
		1=B	2=E	3=C	-	-	-	
BCR101F*	UCs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR101L3*	UC	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR101T*	UCs	1=B	2=E	3=C	-	-	-	SC75

\*Preliminary

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Emitter-base voltage	$V_{EBO}$	10	
Input on voltage	$V_{i(on)}$	50	
Collector current	$I_C$	50	mA
Total power dissipation- BCR101F, $T_S \leq 128^\circ\text{C}$ BCR101L3, $T_S \leq 135^\circ\text{C}$ BCR101T, $T_S \leq 109^\circ\text{C}$	$P_{tot}$	250 250 250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$		K/W
BCR101F		≤ 90	
BCR101L3		≤ 60	
BCR101T		≤ 165	

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics**

Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{V}, I_C = 0$	$I_{EBO}$	-	-	75	$\mu\text{A}$
DC current gain <sup>2)</sup> $I_C = 5 \text{mA}, V_{CE} = 5 \text{V}$	$h_{FE}$	70	-	-	-
Collector-emitter saturation voltage <sup>2)</sup> $I_C = 5 \text{mA}, I_B = 0.25 \text{mA}$	$V_{CEsat}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{V}$	$V_{i(off)}$	0.5	-	1.8	
Input on voltage $I_C = 1 \text{mA}, V_{CE} = 0.3 \text{V}$	$V_{i(on)}$	1	-	3	
Input resistor	$R_1$	70	100	130	$\text{k}\Omega$
Resistor ratio	$R_1/R_2$	0.9	1	1.1	-

**AC Characteristics**

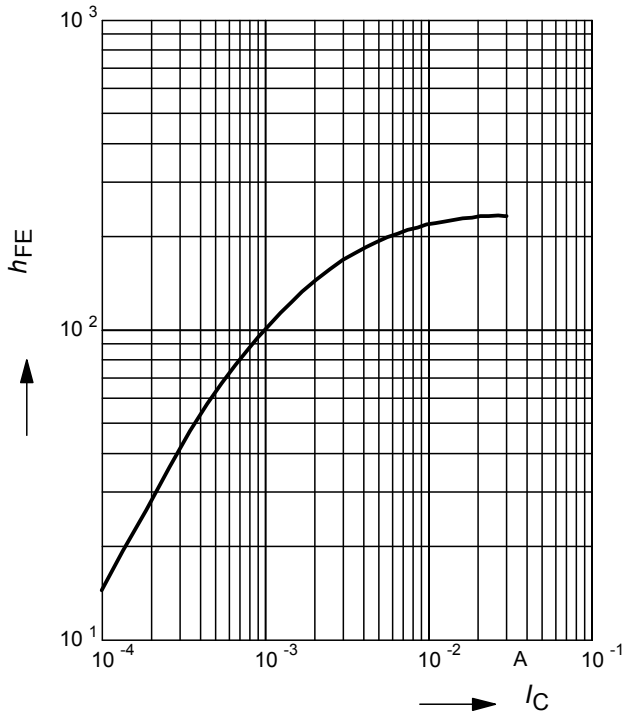
Transition frequency $I_C = 10 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	$f_T$	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{V}, f = 1 \text{MHz}$	$C_{cb}$	-	3	-	pF

<sup>1</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

<sup>2</sup>Pulse test:  $t < 300 \mu\text{s}$ ;  $D < 2\%$

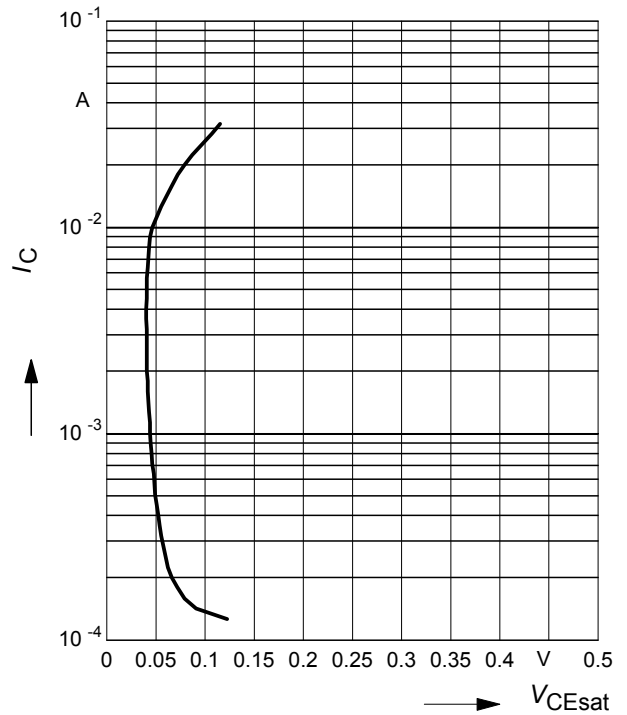
**DC current gain  $h_{FE} = f(I_C)$**

$V_{CE} = 5\text{ V}$  (common emitter configuration)



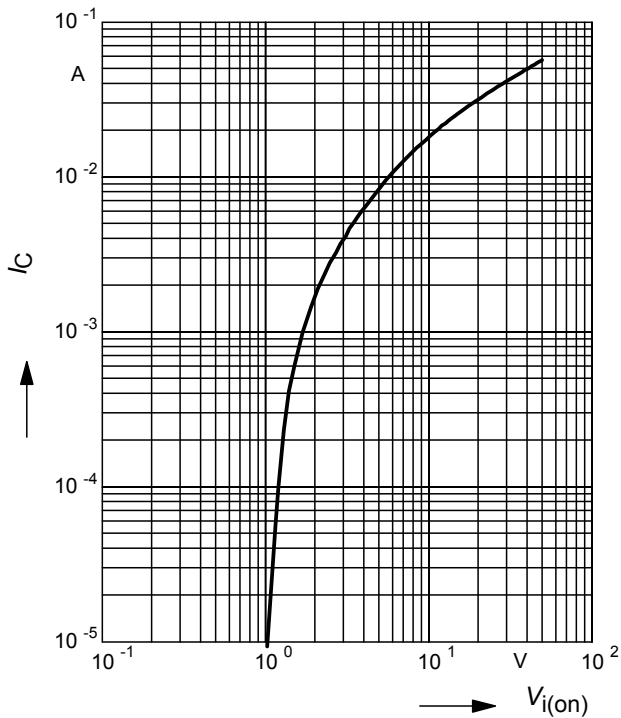
**Collector-emitter saturation voltage**

$V_{CEsat} = f(I_C), h_{FE} = 20$



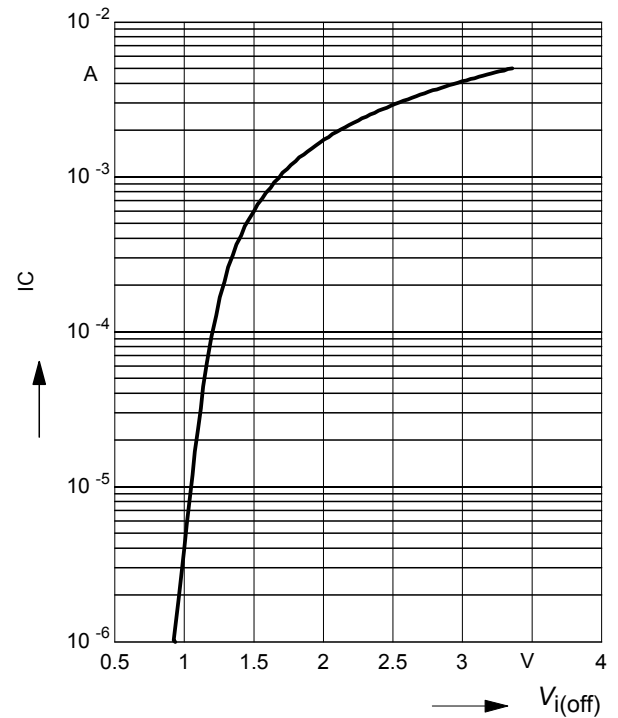
**Input on Voltage  $V_{i(on)} = f(I_C)$**

$V_{CE} = 0.3\text{ V}$  (common emitter configuration)



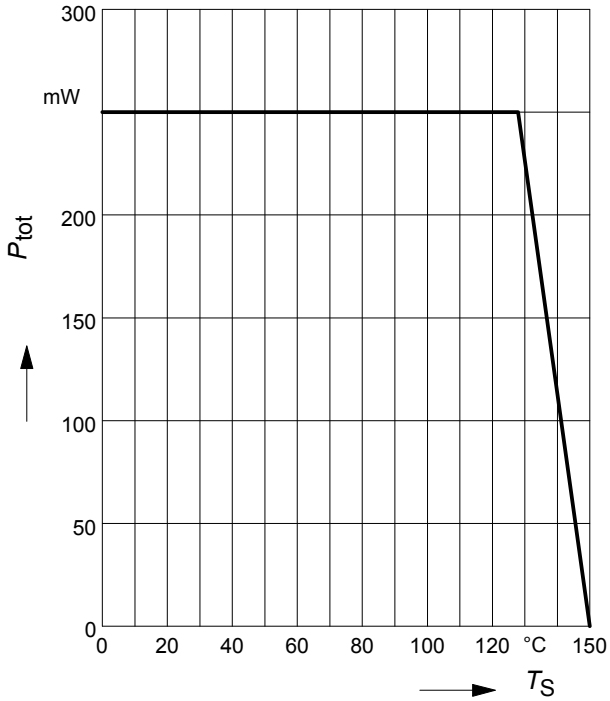
**Input off voltage  $V_{i(off)} = f(I_C)$**

$V_{CE} = 5\text{ V}$  (common emitter configuration)



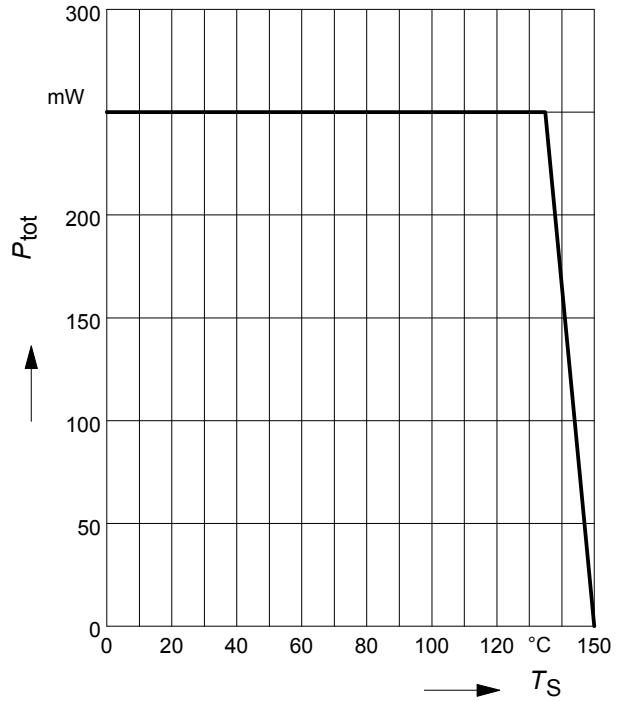
Total power dissipation  $P_{tot} = f(T_S)$

BCR101F



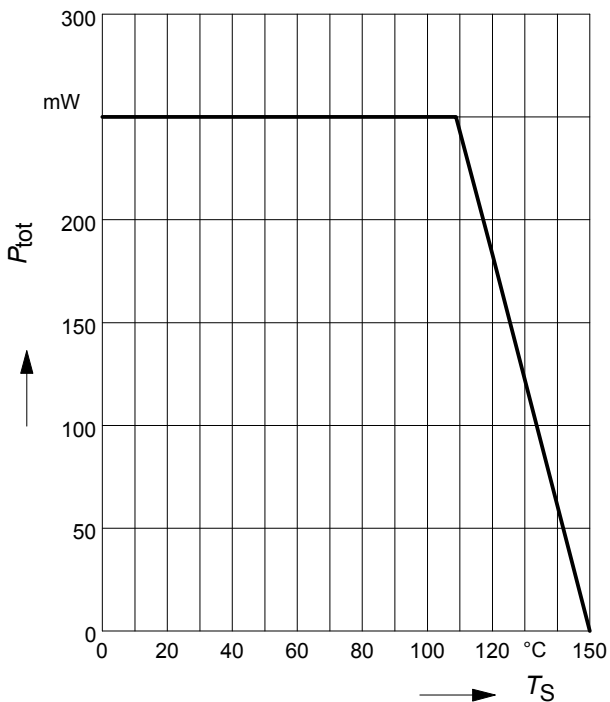
Total power dissipation  $P_{tot} = f(T_S)$

BCR101L3



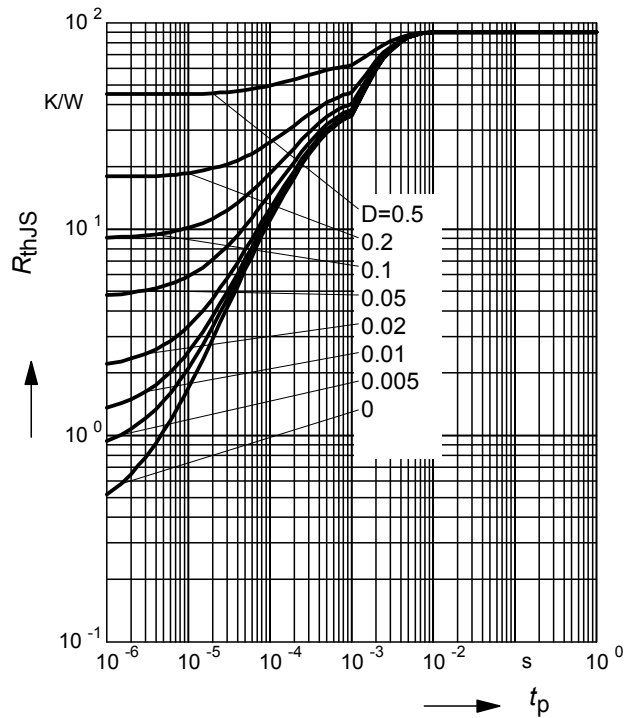
Total power dissipation  $P_{tot} = f(T_S)$

BCR101T



Permissible Puls Load  $R_{thJS} = f(t_p)$

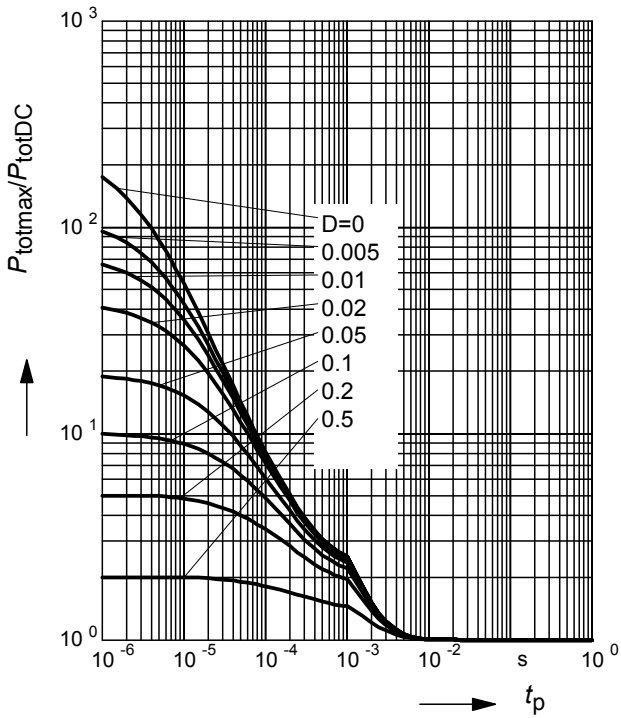
BCR101F



**Permissible Pulse Load**

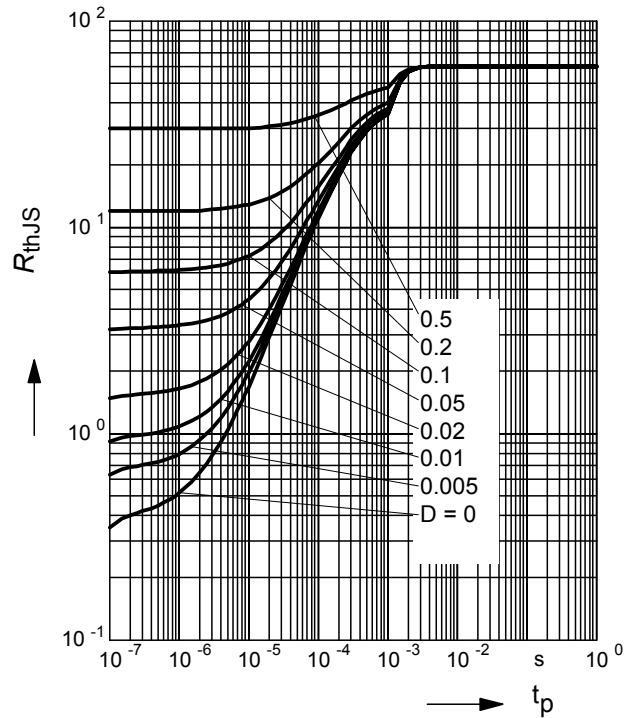
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR101F



**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$**

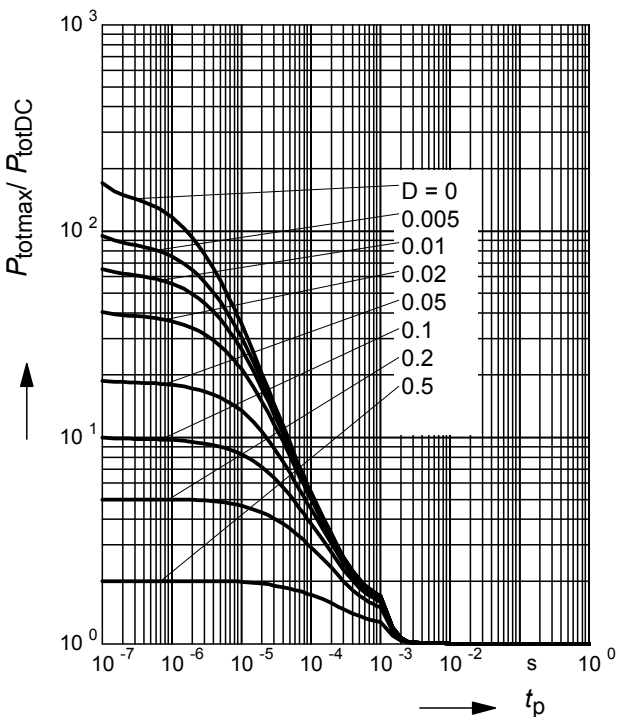
BCR101L3



**Permissible Pulse Load**

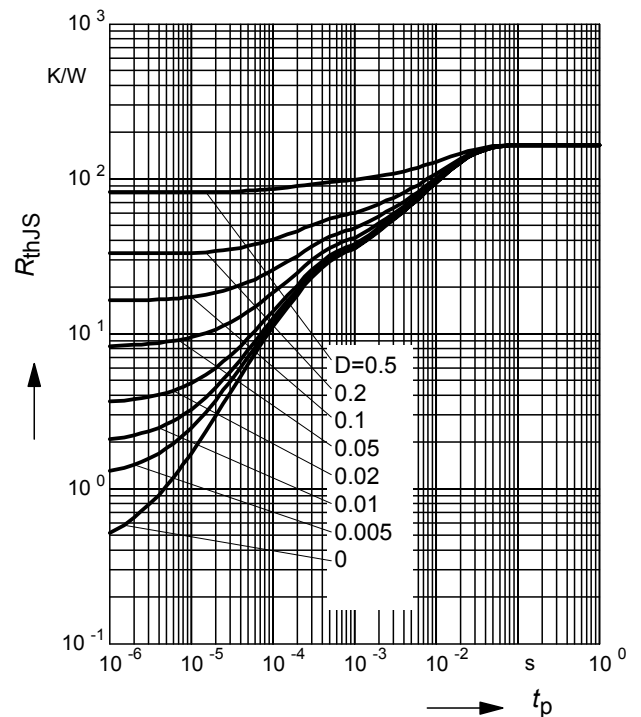
$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR101L3



**Permissible Puls Load  $R_{\text{thJS}} = f(t_p)$**

BCR101T



**Permissible Pulse Load**

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$$

BCR101T

